

Libert & Associates
3 Mill Pond Lane
Powder Forest Business Park
P.O. Box 538
Simsbury, Connecticut 06070-0538

Official**FAX MESSAGE****FAX RECEIVED**

JUL 20 2001

FROM: Frederick A. Spaeth

DATE: July 20, 2001

GROUP 3600

ATTY DOCKET: P-1583

SER. NO. 09/470,343

TO:	FAX NUMBER:	(*)
1. Ms. Diana Bates U.S. Patent and Trademark Office	(703) 305-7687	()
2.		()
3.		()
4.		()

(*) "x" indicates that a mail copy of this transmission follows.

TOTAL PAGES TRANSMITTED, INCLUDING THIS COVER SHEET: **2**

If there are any difficulties with this transmission, please call: (860) 651-9321

Transmit return facsimile messages to: (860) 651-5735

Cover Sheet Message:

Dear Ms. Bates:

Enclosed is a copy of the signature page of the amendment filed on July 6, 2001 in the captioned application. Thank you for your attention to this matter.

Yours truly,



Frederick A. Spaeth
Registration No. 33,793

IMPORTANT NOTICE

The information contained in this facsimile message is private, privileged and confidential and may be used only by the addressee(s). If you are an unintended recipient of this message, you are requested to immediately contact this office by telephone (collect call) or fax at the above number(s) to arrange for our retrieval of the message at no cost to you.

-7-

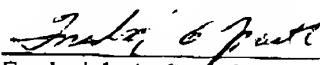
not impede the plasma generated from the silicon bridge from igniting the energetic material. For this reason, by employing titanium in place of tungsten, the resulting invention provides an advantage not recognized in the cited references, i.e., the claimed device will initiate the reactive material much more reliably than prior art devices. It will be understood by one of ordinary skill in the art, upon a reading and understanding of the captioned application, that this advantage could be realized by employing any metal having a melting temperature well below the vaporization temperature of the semiconductor material. For this reason, claims 21, 22 and 23 need not be limited to titanium.

New dependent claim 22 adds further detail to claim 21, specifically defining a procedure which makes use of the relative melting and vaporizing temperatures of titanium and a typical semiconductor material such as silicon.

New dependent claim 23 specifies the use of a metal that is reactive with oxygen to provide the advantage described in the application at page 4, lines 21-28, i.e., that the reaction with oxygen contributes thermal energy towards vaporizing the semiconductor bridge and so reduces the energy requirement for the electrical firing signal. It would be understood by one of ordinary skill in the art, upon a reading and understanding of the captioned application, that this benefit can be attained by the use of oxygen-reactive metals other than titanium.

The stated rejection has been traversed by the foregoing amendments and remarks. Re-examination of the application is respectfully requested.

Respectfully submitted,



Frederick A. Spaeth
Registration No. 33,793
Attorney for Applicant

Libert & Associates
3 Mill Pond Lane
P.O. Box 538
Simsbury, CT 06070-0538

Telephone: (860) 651-9321
Facsimile: (860) 651-5735

P-1500s/P-1583/rcsponse(mf)